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P-CHANNEL ENHANCEMENT MODE MOSFET

Features

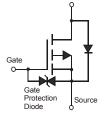
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

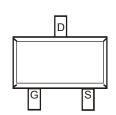
- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (approximate)







Drain



Top View

Equivalent Circuit

Top View

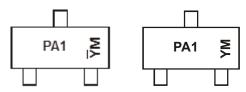
Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1013UW-7	SOT-323	3000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



PA1 = Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) \overline{Y} M = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Year	2008	2	009	2010	2	2011	2012		2013	2014		2015
Code	V		W	Χ		Υ	Z		Α	В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Char	Symbol	Value	Unit		
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±6	V
Continuous Drain Current (Note 5)	Steady State	T _A = +25°C T _A = +85°C	I _D	-0.82 -0.54	А
Pulsed Drain Current (Note 6)	I _{DM}	-6	Α		

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	0.31	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	398	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

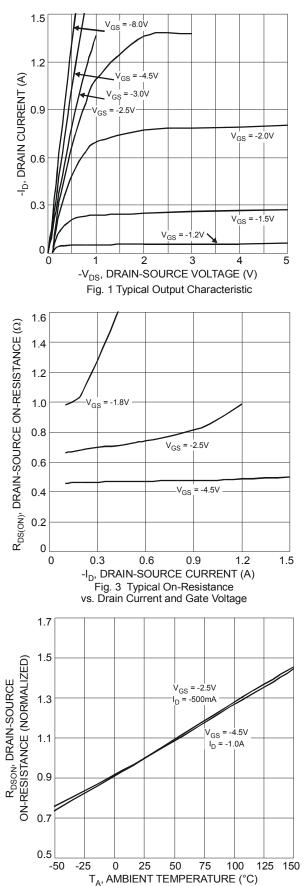
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

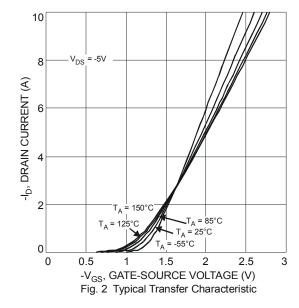
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	1	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	-	-	±2.0	μΑ	$V_{GS} = \pm 4.5 V, V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-1.0	٧	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			0.5	0.75		$V_{GS} = -4.5V$, $I_D = -430mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	0.7	1.05	Ω	$V_{GS} = -2.5V$, $I_D = -300$ mA
			1.0	1.5		$V_{GS} = -1.8V$, $I_D = -150mA$
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	$V_{DS} = -10V, I_{D} = -250mA$
Diode Forward Voltage	V_{SD}		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	59.76	-	рF	101/11/ 01/
Output Capacitance	Coss	-	12.07	-	pF	$V_{DS} = -16V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C _{rss}	-	6.36	-	pF	1 - 1.0WHZ
Total Gate Charge	Qq	-	622.4	-	рC	45)/ 10)/
Gate-Source Charge	Qgs	-	100.3	-	рC	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q _{gd}	-	132.2	-	рC	$I_D = -250 \text{mA}$
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	101/11/
Turn-On Rise Time	t _r	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	$R_L = 47\Omega, R_G = 10\Omega,$
Turn-Off Fall Time	t _f	-	20.7	-	ns	-I _D = -200mA

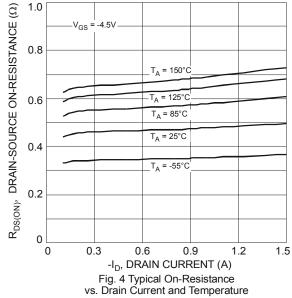
Notes:

- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.









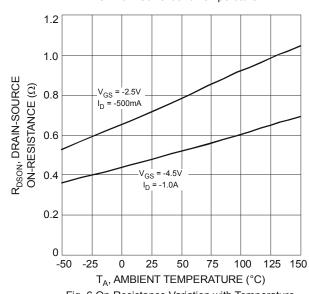


Fig. 5 On-Resistance Variation with Temperature



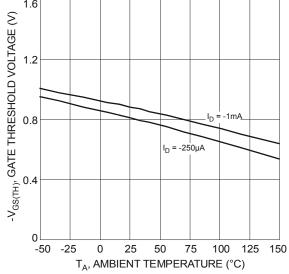
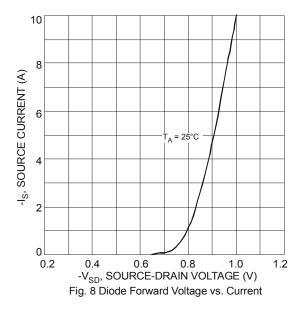
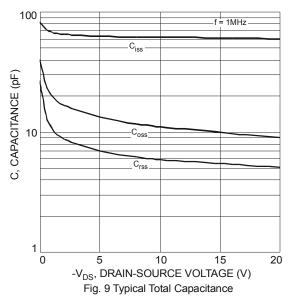


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





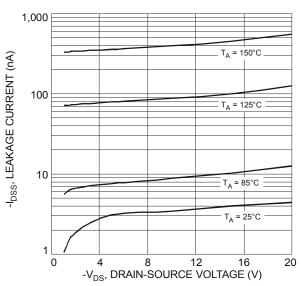


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

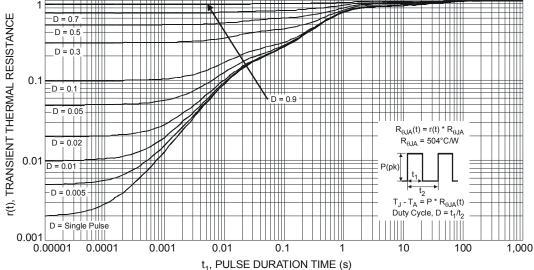
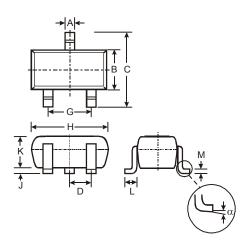


Fig. 11 Transient Thermal Response



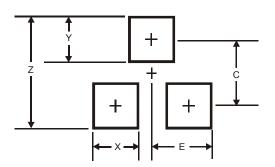
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
Е	1.0

SOT-323 Min

0.25

1.15

2.00

1.20

1.80

0.0

0.90

0.25

0.10

All Dimensions in mm

Max

0.40

1.35

2.20

1.40

2.20

0.10

1.00

0.40

0.18

Тур

0.30

1.30

2.10 0.65

1.30

2.15

0.05

0.95

0.30

0.11

Dim

Α

В

С

D

G

K

М

α



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